NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE60H15A uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

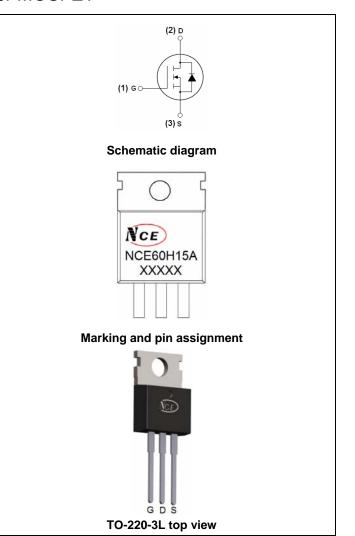
- V_{DS} =60V, I_{D} =150A $R_{DS(ON)}$ <4.0m Ω @ V_{GS} =10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% AVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60H15A	NCE60H15A	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	150	Α
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	105	Α
Pulsed Drain Current	I _{DM}	600	Α
Maximum Power Dissipation	P _D	220	W
Derating factor		1.47	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	900	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

NCE60H15A

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{eJC}	0.68	°C/W	1
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Electrical Characteristics (T_C=25°C unless otherwise noted)

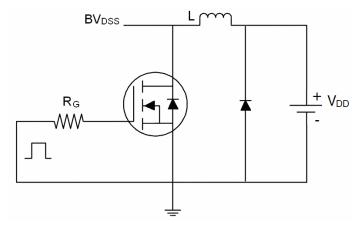
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	<u>.</u>					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	_	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =75A	-	3.1	4.0	mΩ
Forward Transconductance	g FS	V _{DS} =50V,I _D =75A	80	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}		-	5451	-	PF
Output Capacitance	Coss	V _{DS} =30V,V _{GS} =0V,	-	609	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	488	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	25	-	nS
Turn-on Rise Time	t _r	V_{DD} =30V, R_L =0.4 Ω	-	23	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =2.5 Ω	-	90	-	nS
Turn-Off Fall Time	t _f		-	38	-	nS
Total Gate Charge	Qg	\/ 00\/ 75A	-	130.8		nC
Gate-Source Charge	Q _{gs}	V_{DS} =30V, I_{D} =75A, V_{GS} =10V	-	22.8		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	56.9		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =75A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	150	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 75A	-	-	60	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	-	80	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negl	igible (turi	n-on is do	minated b	y LS+LD)

Notes:

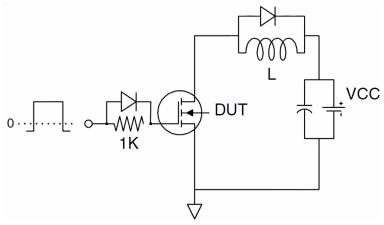
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- **4.** Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}\text{C}$,VDD=30V,VG=10V,L=0.5mH,Rg=25 Ω

Test circuit

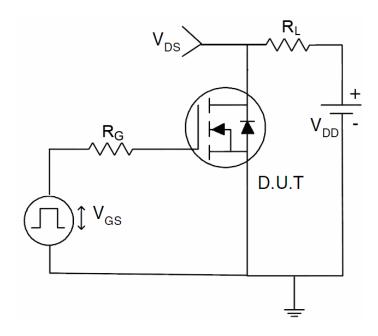
1) E_{AS} test Circuits



2) Gate charge test Circuit:

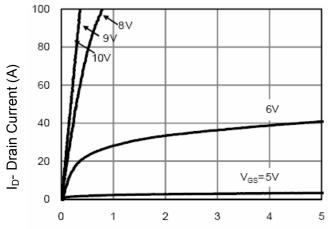


3) Switch Time Test Circuit:





Typical Electrical and Thermal Characteristics (Curves)



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics

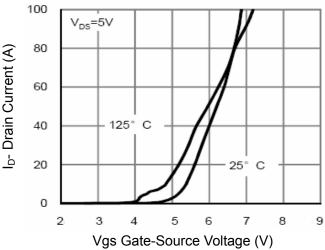


Figure 2 Transfer Characteristics

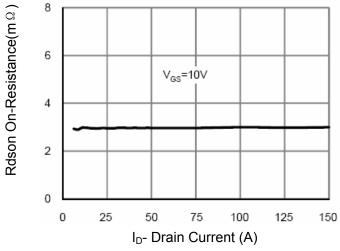


Figure 3 Rdson- Drain Current

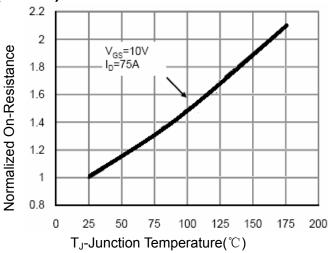


Figure 4 Rdson-JunctionTemperature

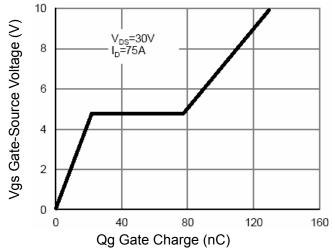


Figure 5 Gate Charge

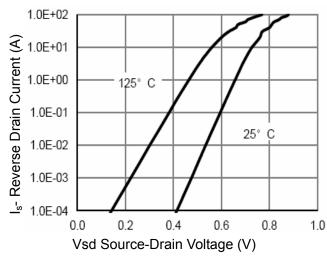


Figure 6 Source- Drain Diode Forward



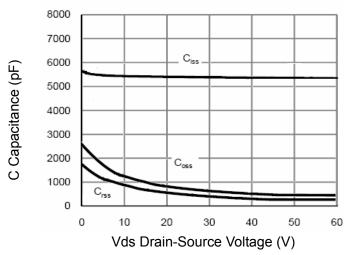


Figure 7 Capacitance vs Vds

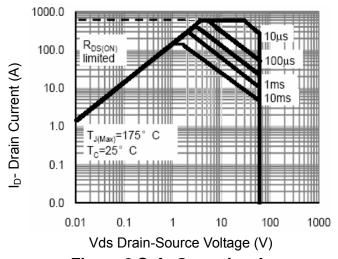


Figure 8 Safe Operation Area

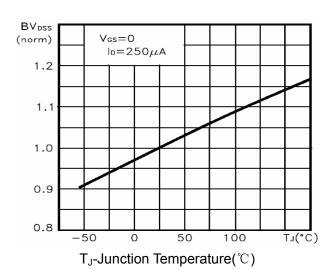


Figure 9 BV_{DSS} vs Junction Temperature

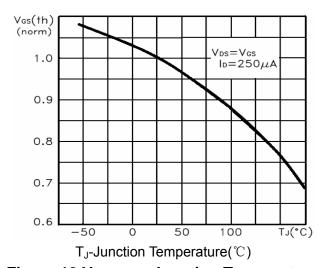


Figure 10 V_{GS(th)} vs Junction Temperature

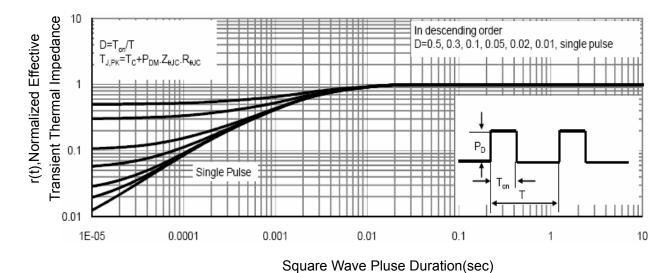
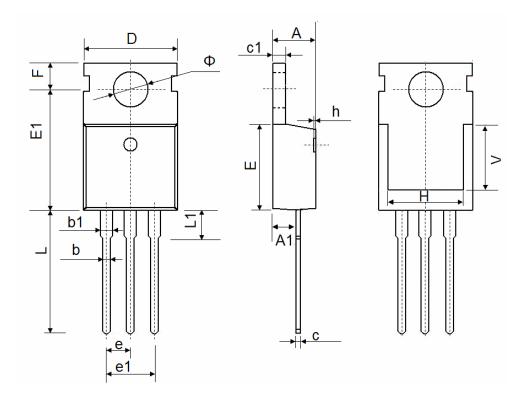


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Complete	Dimensions	s In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.54	I0 TYP.	0.100	TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.50	7.500 REF. 0.295 REF.		REF.	
Ф	3.400	3.800	0.134	0.150	



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